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Self-planarized quantum-disks nanowires ultraviolet-B emitter utilizing pendeo-epitaxy

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The growth of self-assembled, vertically oriented and uniform nanowires (NWs) has remained a challenge for efficient light-emitting devices. Here, we demonstrate dislocation-free AlGa_xN NWs with spontaneous coalescence, which are grown by plasma-assisted molecular beam epitaxy on an n-type doped silicon (100) substrate. A high density of NWs (filling factor > 95%) was achieved under optimized growth conditions, enabling device fabrication without planarization using ultraviolet (UV)-absorbing polymer materials. UV-B (280–320 nm) light-emitting diodes (LEDs), which emit at ~303 nm with a narrow full width at half maximum (FWHM) (~20 nm) of the emission spectrum, are demonstrated using a large active region ("active region/NW length-ratio" ~ 50%) embedded with 15 stacks of Al_xGa_{1-x}N/Al_yGa_{1-y}N quantum-disks (Qdisks). To improve the carrier injection, a graded layer is introduced at the AlGa_xN/GaN interfaces on both p- and n-type regions. This work demonstrates a viable approach to easily fabricate ultra-thin, efficient UV optoelectronic devices on low-cost and scalable silicon substrates.

Introduction

Ultraviolet (UV) light emitting diodes (LEDs) and lasers have attracted considerable attention for applications in sterilization, environmental cleaning, medicine, and lighting, among other fields.¹ AlGa_xN-based UV LEDs, which cover the spectrum of 210–360 nm, can be used to replace the mercury lamp, which contains environmentally hazardous materials. Although tremendous progress has been made on AlGa_xN-based light-emitting devices, such as LEDs and lasers, UV emitters still have low illumination power and low efficiency.² The unresolved material-related challenges and problems are a lack of efficient p-type doping in high-Al-content AlGa_xN, high threading dislocations and defect densities in planar UV LEDs grown on foreign substrates, and low light extraction efficiency (less than 10%).^{3,4}

Recently, researchers have proposed an alternative path to achieve high-efficiency UV LEDs⁵ and lasers^{6–8} using AlGa_xN nanowire (NW) structures. Considerable progress has been made in NWs (NWs)-based UV LEDs and lasers because of the superior crystalline quality (dislocation free) of the AlGa_xN NW and the surface-enhanced p-type dopant (Mg) incorporation.⁹ In their simulation, Mehrdad *et al.* recently reported that light extraction efficiency of up to 70%

could be achieved using the NWs-based platform due to the light scattering and reduced absorption.¹⁰ However, non-radiative recombination at the surface of the NW structures can be a primary cause of the low internal quantum efficiency (IQE) of InGa_xN-based NWs LEDs due to the high surface-to-volume ratio. The AlGa_xN core-shell structure, which acts as a self-passivation AlGa_xN layer, has been reported to provide superior carrier confinement and motivation for realizing high-efficiency UV LEDs.^{11,12}

Nevertheless, most AlGa_xN or InGa_xN NWs have been grown on foreign substrates.^{5,6,13–15} The challenge of their implementation in practical devices is directly related to the fabrication of such NW-based optical devices using a low-cost, scalable and controllable process. Because of the difficulty in controlling the height uniformity, surface morphology of NWs, twist/tilt in crystal orientation and filling factor of nanostructures, researchers must use polymers for surface planarization to make ohmic contacts. Making good ohmic contacts is even more challenging for UV and deep UV LEDs because of the limited availability of UV-transparent polymers. Recently, Le *et al.* demonstrated the controlled coalescence of an AlGa_xN NW array on GaN-on-sapphire substrates; however, the process required a substrate-patterning process using a Ti mask to achieve high coalescence of AlGa_xN NWs for the p-type metal deposition.¹⁶ A similar coalescence technique has been adopted for Ga_xN-based nanocolumn UV devices to reduce the fabrication complexity.¹⁷ In addition, the majority of previous AlGa_xN-based NWs devices have focused more on spontaneously formed AlGa_xN NWs heterostructures in the form of either double heterostructures (DHS) using polarization induced doping configuration^{18,19} or conventional PIN DH structure.^{5,6} Few

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Fig. 1 (a) Top-view SEM image of the device structure, and tilted-angle SEM of the NWs in the inset; (b) STEM-HAADF image of the coalesced AlGaIn NWs with the corresponding schematic showing the layer structure of the NWs LED.

studies have discussed $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{Al}_y\text{Ga}_{1-y}\text{N}$ multiple quantum-disks (Qdisks), which should have superior carrier confinement and thus improve the optical performance of the device.^{17, 20, 21}

In this work, we demonstrate high-density, spontaneously coalesced, dislocation-free AlGaIn NWs that were grown on a silicon (100) substrate using MBE. The optimized growth conditions enabled us to realize self-planarized NWs with a (0001) orientation and a filling factor greater than 95%. As a result, the p-metal contacts can be formed without the planarization step. Furthermore, we grew 15 pairs of $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{Al}_y\text{Ga}_{1-y}\text{N}$ Qdisks, which occupy nearly half the volume of the entire NW, and a notably thin p-type AlGaIn electron-blocking layer. Finally, a p-type graded AlGaIn layer (~25 nm) and a p-GaN layer (~20 nm) were grown as a top contacting layer. This large ratio of the active region to the entire NW creates more opportunities for the injected electrons and holes to recombine in the Qdisks area. The thin p- $\text{Al}_x\text{Ga}_{1-x}\text{N}$ layer on the active region provides a better opportunity for photons to escape from the top surface. In addition, well-aligned Qdisks were observed across the length of the NWs because of the highly uniform height of the AlGaIn NWs. Detailed scanning transmission electron microscopy (STEM) studies revealed the high crystalline quality and nanocluster formation in Qdisks, which helps to promote high carrier localization²² and quantum confinement.^{20, 23} An AlGaIn Qdisks-in-NWs LED that emitted at 303 nm at room temperature was demonstrated. A narrow linewidth emission spectrum was obtained at 48 A/cm² bias (120 mA over an area of 0.5×0.5 mm²) with an full width at half maximum (FWHM) of ~20 nm. The turn-on voltage was 9 V, and the rectification ratio was large for AlGaIn Qdisks LEDs, which are comparable to the LEDs grown on Si substrates with similar emission wavelengths. The electroluminescent (EL) signal was collected with up to 200 mA DC injection using a UV objective. The Nextnano³-based simulation showed an overlap of 42% in the strain-relieved 3D structure, which resulted in a high radiative recombination rate.

Experimental

The UV NWs p-i-n LED structure was grown catalyst-free using Veeco Gen 930 plasma-assisted molecular-beam epitaxy system (PAMBE). The native oxide was removed from Si (100) using a HF-H₂O solution. The Si wafer was first outgassed in the load lock at 200 °C using an infrared (IR) filament to remove any water component. Then, outgassing at 650 °C was performed in the buffer chamber to remove

the organic-based contaminants. In the growth chamber, the wafer was ramped up to 900 °C for 30 min. Upon ramping down, the 1×1 surface reconstruction was observed at ~800 °C, which confirms the absence of any oxide layer. During this process, the wafer was kept facing away and was only brought in line with the sources immediately before the growth initiation. This maintained a uniform coverage of pre-oriented silicon nitride (Si_3N_4) layer on the surface of Si substrates. The resulting orientation and density of the nucleated seeds will affect the height uniformity and degree of coalescence as growth proceeds.

The key to achieving such nearly dislocation-free coalescence NWs is the precise control of the initial GaN nucleation process and growth condition. NWs morphology and areal density can drastically change depending on the growth parameters such as: (a) NWs areal density decreases with substrate temperature and increases with total metal flux;^{24, 25} (b) NWs diameter increases with density of active nitrogen species;²⁶ (c) NWs height is inversely proportion to the substrate temperature;^{24, 26} (d) directionality of NWs depends on the nucleating or pre-orienting layers, such as AlN, and Si_3N_4 ; (e) a higher aspect ratio of NWs can be achieved with increasing flux ratio (V/III) and temperature²⁷ and (f) crystal polarity may be affected by flux ratio, wetting layer and buffer layer.^{28, 29}

In this investigation, the Si-doped GaN layer (150 nm) was firstly nucleated on top of the silicon wafer at 690 °C to improve the crystal quality and achieve the required NWs density. The aluminium flux was then increased to achieve compositional grading from GaN to $\text{Al}_{0.5}\text{Ga}_{0.5}\text{N}$ (over ~20 nm) and avoid any abrupt energy barrier for the electrons. Subsequently, a 75 nm Si-doped AlGaIn layer was grown to provide a larger bandgap for the quantum confinement. The temperature was increased to 740 °C to grow the AlGaIn layer. Then, an active region with 15 stacks of ~2.5 nm $\text{Al}_{0.3}\text{Ga}_{0.7}\text{N}$ Qdisks separated by ~7 nm $\text{Al}_{0.5}\text{Ga}_{0.5}\text{N}$ quantum barriers (QB) was grown on the n-AlGaIn layer. For the active region, the Al flux was fixed at 2×10^{-8} Torr, whereas the Ga flux was alternated between 2×10^{-8} and 4.5×10^{-8} Torr for the QB and Qdisk, respectively. A 10 nm magnesium (Mg)-doped EBL layer was grown. Then, $\text{Al}_{0.6}\text{Ga}_{0.4}\text{N}$ was graded down to the GaN layer. As with the n-type AlGaIn grading layer, grading (~20 nm) was performed to improve the hole injection and reduce absorption losses.³⁰⁻³² The device was completed with a 10-nm Mg-doped GaN layer as the p-type contact layer. The nitrogen flow was maintained at 1 sccm with a fixed RF power of 350 W to optimize the

Fig. 2 (a) HAADF-STEM image of single NWs. (b) Concurrently acquired ADF signal and Ga-map from nanoscale EELS-SI (boxed in the blue dashed line in (a)), which show a direct correspondence between the local increases in the Ga signal and ADF signal within the signal atomic planes. (c) High-magnification atomic-resolution HAADF image of the selected region (boxed in the green dashed line) in (a). (d) Elemental mapping from the EELS spectrum in the green area marked in (c). (e) Elemental mapping from EELS-SI of the red area marked in (a) of group-III elements, which were extracted from Ga $L_{2,3}$, Al $L_{2,3}$, the acceptor Mg $L_{2,3}$ and the concurrently acquired ADF signal from nanoscale EELS-SI. (f) High-magnification atomic-resolution image of the interface between the GaN NW and silicon (001) substrate.

NWs shape and density. A top-view scanning electron microscopic (SEM) image of the AlGaIn NWs is shown in Fig. 1 (a). The diameter and length of the NWs were measured to be ~ 70 and 400 nm, respectively.

SEM and TEM were used to investigate the quality and structure of the NWs. An FEI Titan 80-300 ST microscope was used for the TEM characterization. The microscope was operated at an accelerating voltage of 300 keV. The atomic-number-sensitive (Z-contrast) high-angle annular dark-field (HAADF) STEM images of the NWs were obtained. The strain field in the Qdisks was obtained using a geometrical phase analysis (GPA) analysis. The compositional variation of group-III elements (Al $L_{2,3}$ and Ga $L_{2,3}$) and the Mg distribution in the NWs across different interfaces and layers were studied using elemental mapping by electron energy-loss spectroscopy (EELS) in the STEM mode. A weighted principal-components analysis (PCA) was applied to reduce the noise in the spectrum images using the MSA plugin in Digital Micrograph by HREM Research Inc.

Before the devices were fabricated, the room temperature photoluminescence (RTPL) was measured using a 266 nm excitation pulse laser (SNU-20F-100) in a reflective mode configuration. The PL signal was collected by a UV objective and beam splitter and subsequently focused into the Andor monochromator (SR-750). A 266-nm notch filter was used to filter off laser radiation. A cooled (-80 °C) iDUS silicon detector, which was connected to the monochromator, was used to measure the signal.

The UV NWs LEDs were modeled using the commercial Nextnano³ software.³³ The band diagram of the structure was obtained by self-consistently solving Poisson's, Schrödinger's, current continuity, and carrier transport equations under forward bias. For the valence band, the 6×6 $k \cdot p$ method was used to consider the non-parabolic nature of the energy bands. The effects of the wave function overlap, carrier dynamics in the AlGaIn-based active region and polarization-induced band bending because of the interface fixed charges were also considered.

The UV NW LEDs were fabricated using the standard UV contact lithography process. First, the NWs were cleaned with a buffered oxide etch (BOE) solution to remove any oxide layer formation. Ni (15

nm) / Au (10 nm) layers were directly deposited on top of the coalesced p-GaN layer without a planarization process, which formed an ohmic contact with p-GaN, upon annealing at 600 °C in O₂ gas for 1 min. The thickness of the Ni/Au layer was used to spread the current well while being transparent to emitted UV light. Then, a thick Ni (10 nm) / Au (1 μm) layer was deposited as the top p-contact pad for probing. Silicon was etched 200 nm from the back to expose a clean, unoxidized surface. For the back contact, Ti (10 nm) / Au (150 nm) were sputtered as the n-pad. Then, the device was annealed again in N₂ gas at 250 °C for 1 min to form an n-type ohmic contact. The electroluminescent (EL) signal was measured using the PL setup with a camera attached to the beam splitter mount. A Keithley source 2450C device was used to inject a continuous current into the device.

Results and discussion

Fig. 1(a) includes a high-magnification and cross-sectional SEM (CSSEM) image of AlGaIn NWs. The coalescence of the top p-GaN layer is observed. This configuration improves the current spreading and injection and reduces carrier leakage without filling and planarizing materials, such as polyimide or parylene, which are commonly used in the fabrication process of NW-based devices.^{34, 35} The CSSEM image clearly shows that the NWs were largely vertically aligned along the c-axis and had a uniform height distribution over a large area. A high density of $\sim 1 \times 10^{10} \text{ cm}^{-2}$ of NWs with a filling factor above 95% was estimated. Fig. 1(b) provides a schematic diagram of the detailed structure of the NWs UV LED and an HAADF cross-sectional image of an array of AlGaIn NWs. The brighter regions correspond to the Ga-heavy areas, which are the bottom n-type GaN, AlGaIn/AlGaIn Qdisks active regions, and the top p-GaN layer. The NWs were vertically aligned and closely spaced but disjointed along the active region, which demonstrates the good growth conditions. No threading dislocation or stacking faults were observed.

Fig. 2(a) shows the HAADF-STEAM image of a single NW, which includes the n-type AlGaIn layer, an active region, a p-type AlGaIn electron-blocking layer (EBL), a top AlGaIn grading layer and a p-GaN layer. Well-defined uniform 15 Al_{0.3}Ga_{0.7}N Qdisks (2.5 nm) were sandwiched between Al_{0.5}Ga_{0.5}N (7.1 nm) layers. The NWs exhibit an inverse tapered shape, where they are thinnest at the bottom (~ 30 nm) and have a diameter of 60 nm at the top. This shape was attributed to two main reasons: the variation in growth temperature as growth proceeds and the slight lateral-growth preference because of the high Ga adatom mobility. A close examination of the NW sidewall shows the AlGaIn encapsulation. This AlGaIn shell has been reported to form because of the small diffusion length of aluminum, which promotes lateral growth.^{5, 6, 36} When the NWs were grown, the growth temperature was stabilized before nucleation and the active region to ensure uniform Qdisks across the active region. No threading dislocation and stacking faults are observed. Fig. 2(b) shows a further study on the formation of nanoclusters in each Qdisk. The Ga-map (displayed in temperature scale) and concurrently acquired ADF signal from nanoscale EELS spectrum imaging (EELS-SI) (boxed in the blue dashed line in Fig. 2(b)) show a direct correspondence between the local increases in the Ga signal and ADF signal in the signal atomic planes. This correspondence

indicates the formation of nanoclusters in Qdisks, which might cause a strong quantum confinement effect related to the compositional fluctuations of the active region. Planar InGaIn-based LEDs have been reported to achieve high efficiency because of the highly localized excitons, which are created by indium segregation.³⁷ Thin-film AlGaIn-based UV light-emitting devices have achieved large optical gains with an extremely low optical pumping threshold via the introduction of high-density nanocluster-like features in the AlGaIn wells.³⁸ Strong stimulated emission²² and high-efficiency LEDs were produced by containing nanometer-scale compositional inhomogeneities in AlGaIn thin films. Recently, the quantum-dot-like behavior of the compositional fluctuations³⁹ and three-dimensional quantum confinement in AlGaIn double heterostructure NWs has been observed in achieving UV light emitters.⁶ This work clearly demonstrates that high-crystal-quality AlGaIn NWs with nanoclusters embedded in Qdisks can be widely applicable to achieve high-efficiency LEDs. Fig. 2(c) shows a high-magnification atomic-resolution HAADF image of the selected region (boxed in the green dashed line) in Fig. 2(a). This image presents a typical AlGaIn core-shell structure (low Al content in the core of the NW and high Al content near the surface of the NW (dark region)). This Al-rich AlGaIn shell was further surrounded by a few-atomic-plane-thick Ga-rich AlGaIn outermost shell. The formation of the AlGaIn shell was mainly ascribed to the Al adatom migration, which occurred more slowly than that of Ga adatoms and caused Al accumulation along the NW surface. This shell was further confirmed in Fig. 2(d), which shows the elemental mapping of the Ga L_{2,3} and Al L_{2,3} edges from EELS-SI of the green area in Fig. 2(c), which confirms the formation of an AlGaIn core-shell structure. As reported by others, the formation of such Al-rich AlGaIn in the near-surface region can improve the carrier confinement, reduce the surface states because of the self-passivated layer, and significantly suppress the nonradiative surface recombination, which results in a high internal quantum efficiency of 70~80% for the NW LEDs and lasers.⁵ Fig. 2(e) shows an elemental mapping from the EELS-SI of the red area in Fig. 2(a). The elements extracted from Ga L_{2,3}, Al L_{2,3}, the acceptor Mg L_{2,3} and concurrently acquired ADF signal from nanoscale EELS-SI show the Ga and Al elemental distributions in different layers (red for Ga atom, green for Al atom, and purple for Mg atom). The EELS mapping confirms the gradual decrease in Al content and continuous increase in Ga content in the compositional graded p-AlGaIn layer. The temperature of the Al source was linearly reduced to achieve a logarithmic decrease in aluminum flux; thus, an AlGaIn grading layer was obtained. This graded p-AlGaIn served as a transition layer to avoid creating a high abrupt potential for the holes to inject into the Qdisks while maintaining a small p-GaN thickness to mitigate reabsorption losses. Fig. 2(f) shows a high-magnification atomic-resolution image of the interface between the GaN NW and silicon (100) substrate. There is an extremely thin (1-2 nm) Si₃N₄ monolayer at the GaN NW and silicon interface during the initial nucleation stage. The Si₃N₄ formation is thermodynamically favored, which is commonly observed when similar GaN NWs are directly grown on Si. The thickness of Si₃N₄ was minimized by bringing the substrate into a position facing the sources immediately before the growth.

To understand the distribution of strain for Qdisks in AlGaIn NWs, a GPA was applied to the HR-STEM image of Fig. 3(a) in the region inside the red lines in Fig. 2(a). The strain fields are the derivatives of

the displacement fields along the x- and y-axes and can be defined as follows:

$$e_{xx} = \frac{\partial u_x(r)}{\partial x} = -\frac{1}{2\pi|g_1|} \frac{\partial P_{g1}(r)}{\partial x} \quad (1)$$

$$e_{yy} = \frac{\partial u_y(r)}{\partial y} = -\frac{1}{2\pi|g_2|} \frac{\partial P_{g2}(r)}{\partial y} \quad (2)$$

where e_{xx} , e_{yy} , $u_x(r)$, $u_y(r)$, g_1 , g_2 , $P_{g1}(r)$, and $P_{g2}(r)$ are the in-plane biaxial strains, out-of-plane strain (along the growth direction), displacement field along x, displacement field along y, reciprocal vector along x, reciprocal vector along y, and corresponding phase images, respectively.^{40,41}

Fig. 3 (a) HAADF-HRSTEM images of the three top Qdisks, which are identical to the area enclosed in the green dashed box in Fig. 2(a). (b) Strain map obtained using a geometrical phase analysis for the selected area. (c) Strain profile of the three Qdisks. (d) Simulated biaxial and uniaxial strain of a free-standing NW.

The GPA analysis based on the above formulation was applied to the HAADF-HRSTEM image to determine the strain fields in the AlGaIn NWs. The HAADF-HRSTEM image of three Qdisks is shown in Fig. 3(a), and the corresponding GPA result is shown in Fig. 3(b). Because the strain is considerably relieved in the thick n-AlGaIn layer, the strain was referenced to the AlGaIn barrier, which was assumed to be strain-free. Strain-free AlN NWs have been shown to grow on

Si.⁴² The results in Fig. 3(b) show that a slight build-up of strain is observed in the Qdisks along the growth direction, which is as expected. In addition, the strain in the growth direction was quantified by generating a line profile across the dotted areas in the strain map. The increase in strain in the upper Qdisks may be because of the increase of the total strained Qdisk volume in the growth direction. In addition, the increase in width of the NWs may increase the strain in the Qdisk as the growth proceeds. Nevertheless, the strain in our AlGaIn NWs is considerably smaller than the planar structures with similar Al composition, which paves a new way for achieving highly efficient UV emitters.

The strain in the free-standing NW was calculated as shown in Fig. 3(d). The Qdisks have biaxial tensile strain in the presence of the bottom n-GaN layer. The out-of-plane strain of 0.00019 corresponds well with the measured ~0.0002 strain, as shown in Fig. 3(c). Because the model adopted for calculation minimizes strain energy at the interface of n-GaN/AlGaIn, n-GaN is compressively strained, whereas n-AlGaIn is tensile strained.

Fig. 4 (a) 3D depiction of the UV-emitting NWs with individual layers labeled. (b) RTPL spectrum with peak intensities at ~303, ~314 and ~356 nm, which were emitted from the active region, graded AlGaIn layer, and top and bottom GaIn layers. Red, blue and green are the Gaussian fit spectra for the three peaks.

Fig. 5 (a) Band diagram under a forward bias of 4 V. (b) Wave function profiles that correspond to the electrons and holes in the active region. (c) Polarization-induced fixed charges. (d) Recombination rates including Shockley-Read-Hall (SRH), Auger and direct recombination in the active region. The fourth QW from the n-side is marked with a green box.

Next, we investigated the optical properties of AlGaIn Qdisks in NWs. A 3-dimensional (3D) schematic diagram of the NWs with the respective layers is shown in Fig. 4(a). Fig. 4(b) shows the room-temperature PL of the AlGaIn NWs. A strong PL signal is an indication of the quantum confinement in Qdisk structures with good AlGaIn crystalline quality. The spectrum consists of three Gaussian peaks, which could originate from different layers in the NW. The three peaks that emit at ~ 303 , ~ 314 , and ~ 356 nm at room temperature correspond to the emissions from the active region, graded layer, and GaN contact layer, respectively. The emission from the active region has an FWHM of 14.8 nm, which is related to highly localized carriers in the Qdisks. In reported UV devices based on DHS, it was shown to have considerably broader linewidth than that of this investigation, thus highlighting the advantage of using quantum-confined structures.³⁶ The AlGaIn material is less prone to temperature variations than InGaIn, which has been shown to have a FWHM of more than 50 nm.⁴³ PL peaks from the graded AlGaIn layer and GaN layer have considerably broader FWHMs of 23.8 and 29.4 nm, respectively. This is likely due to the dopants dependent linewidth broadening and therefore band-tailing effect, as well as bandgap variation in the presence of inhomogeneous strain; both effects becoming more prominent with increase in layer thickness. As discussed below, the peak at ~ 303 nm correlates well with the EL

emission at high current injection. A broad but relatively weak peak at approximately 400 nm indicates the recombination through the trap states introduced by Mg impurities in GaN.⁴⁴

The NWs nucleate via strain relaxation through their free surface.^{45, 46} Strain was adjusted in the 1D model to depict the more realistic free standing scenario as shown in Fig. 3(d). In the simulation, the growth direction was assumed to be N-polar, which is an important parameter in determining the direction of polarization fields.⁴⁷ The band offsets $\Delta E_c/\Delta E_v$ were assumed to be 70/30.⁴⁸ Fig. 5(a) shows the calculated band diagram of the AlGaIn Qdisk-based UV NWs LED under a forward bias of 4 V. Fig. 5(b) shows a considerably large wave function overlap of 42% for the electrons and holes because of the suppressed piezo-polarization fields, as shown in Fig. 5(c). The calculated recombination rates in the active region show that the SRH and direct radiative recombination are dominant (Fig. 5(d)). With a further increase in voltage bias, the direct radiative recombination rate is expected to surpass the SRH non-radiative recombination. On the other hand, because of the large number of wells, and reduced average carrier density, the Auger recombination is significantly suppressed. The energy separation of 4.19 eV (296 nm) between the confined carrier states correlates well with the PL and EL peak positions (303.3 nm). A decrease in barrier height is observed by 0.22 eV and 0.3 eV at n-Al_{0.5}Ga_{0.5}N/GaN and p-

Fig. 6 (a) L-I-V characteristics of the NWs UV LED, with the reverse bias characteristics shown in the inset. (b) The calculated EQE of the device. (c) The EL spectrum of the NWs device with a changing current bias of 0–120 mA, and the measurement using an extended wavelength range showing the contribution from GaN (see inset). (d) Variation of the integrated intensities and peak shift (see inset) of the two EL peaks.

$\text{Al}_{0.6}\text{Ga}_{0.4}\text{N}/\text{GaN}$ interfaces by incorporating a graded layer compared to the conventional abrupt interface, which can significantly enhance the carrier injection efficiency of our device.

Fig. 6 (a) presents the current-voltage characteristic of the AlGaIn NWs LED in linear scale. The good diode behavior with a turn-on voltage of 9 V and a large rectification ratio (ratio of the forward bias to the reverse bias current) of $\sim 10^6$ at ± 15 V are observed. In the presence of the adopted coalesced top p-GaN growth scheme, our device shows improved reverse bias behavior compared to more commonly used tilted-angle deposition technique for realizing devices emitting around 300 nm or below.^{5,7} The larger turn-on voltage of 9 V compared to the bandgap of the active region might be because of the Si_3N_4 layer at the GaN/Si interface, smaller p-contact area and reduced doping efficiency in large-bandgap AlGaIn layers in these NWs. In NWs work, turn-on voltages of ~ 5 V to ~ 12 V have been reported with significant improvement obtained when using tunnel junctions.^{7,19,21,49} In comparison, a planar structure having GaN/AlN embedded quantum-dots, emitting at 308 nm, with an estimated IQE of 62 % was demonstrated albeit with considerably larger turn-on voltage of 14 V.⁵⁰ This further highlights the efficient doping in NWs based devices. The optical power at different injection currents can be derived from the L-I measurement, as shown in Fig. 6(a). It may be necessary to have a stable light output

power at high injection levels based on the practical application. The conventional nitride-based planar devices suffer from the “efficiency-droop” phenomenon, which is a degradation of the optical power with an increase in injection current.⁴⁴ As shown in Fig. 6(b), which depicts the calculated EQE plotted against the current, a droop is observed up to an injection current of 80 mA/cm². The device performance can be improved because our device may have the following issues: (1) reduced photon collection efficiency because the device under testing was not placed inside the integrating sphere; (2) low light extraction efficiency in the presence of top metal pad shadow, which covered 40% of the device area, semi-transparent Ni (15 nm)/Au (10 nm) spreading layer and absorbing top p-GaN layer; and (3) poor heat dissipation and current injection in the presence of Si_3N_4 formation. All of these issues can be resolved with further structure design, growth optimization and device fabrication. A photograph of the lighting device is shown in the inset of Fig. 6(b).

The room temperature electroluminescence (EL) spectra of the AlGaIn NW LEDs were collected at different injection currents of 1–120 mA, as shown in Fig. 6 (c). The primary peak from the active region is ~ 303.3 nm with a slight blueshift (~ 1.4 nm) in the range of injected currents, as shown in the inset of Fig. 6(d). The logarithmic plot of the EL intensity, shown in the inset of Fig. 6(c), shows

insignificant emission at approximately 400 nm, which indicates negligible current leakage into the p-GaN layer. A second peak at 338 nm is observed with an FWHM of ~39.2 nm. The large width of this peak indicates the electron-hole recombination process from the graded AlGaN layer.^{18, 19, 51} A similar but relatively weaker peak is also observed in the RTPL spectrum. The integrated intensities of the two EL peaks under different injection currents further verify the origin of the two peaks (see the inset of Fig. 6 (d)). At low injection current, because the mobility of the holes was lower than the mobility of the electrons, more electron-hole pairs were recombined in the graded AlGaN layer and fewer holes reached the Qdisks, which created a stronger 338 nm than the 303 nm peak from the active region. However, with an increase in bias current, increasingly more holes could reach the Qdisks and effectively recombine in these highly localized states. After the current was increased to 40 mA, the radiative recombination across the active region began to dominate, as indicated in the EL spectra. With a further increase in bias current, the peak intensity of 304 nm increased nearly linearly, whereas the peak at 338 nm began to saturate. Fig. 6(d) shows a similar trend of the integrated intensity of the two peaks. The optical performance can be further improved via device optimizations, such as tuning the thickness and Al concentration of the graded AlGaN layer or using large-bandgap insertion layers in the active region to increase the strength of the radiative recombination.⁵²

Conclusions

In summary, UV-B LEDs based on self-planarized AlGaN NWs with embedded Qdisks were demonstrated. The vertically aligned NWs with a large density of $\sim 1 \times 10^{10} \text{ cm}^{-2}$ and coalesced top p-GaN were grown using PAMBE on Si substrates with a large filling factor (>95%). Strong PL and EL emissions from the active region were obtained because of the good crystal quality of the material, reduced polarization fields, and tightly quantum-confined carriers in the Qdisks-in-NWs. The EL peak emission of the Qdisk-based UV LEDs has a small linewidth of 20 nm, which is significantly smaller than that of the conventional DHS-based UV NWs LEDs.

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